



Monocrystalline Silicon Ingot - USA

Technical Specifications

PVINGUSA	
	
Article	Monocrystalline Silicon Round ingots
Origin	USA
Grade	Solar grade,99.9999% 6N purity
Growing Method	Czochraiski(cz) method
Diameter	8 inches
Length	1-1.5 meters
Conductivity	P-type Alloy Dopent boron
Orientation	<100> ±3 degree
Crystal Perfection	Free from grain and twin boundary, swirl slip line and lineage
Dislocation Tendency	<5000atoms/cm3
Dislocation Density	<3000atoms/cm2
Resistivity	0.5-3 ohms cm 3-6 ohms cm (Client to specify)
Redial Resistivity change	<12%
Carbon Content	<5x10 ¹⁶ atoms/cm3
Oxygen Content	<1x 10 ¹⁸ atoms/cm3
Life Time	≥ 10 micro seconds

Monocrystalline Silicon Ingot - China

Technical Specifications

PVINGCH	
	
Article	Monocrystalline Silicon Round ingots
Orgin	China
Grade	Solar grade,99.9999% 6N purity
Growing Method	Czochraiski(cz) method
Diameter	8 inches
Length	1-1.5 meters
Conductivity	P-type Alloy Dopent boron
Orientation	<100> ±1 degree
Crystal Perfection	Free from grain and twin boundary, swirl slip line and lineage
Dislocating Tendency	
Dislocation Density	<3000atoms/cm2
Resistivity	
Redial Resistivity change	<12%
Carbon Content	<5x10 16atoms/cm3
Oxygen Content	<1x 10 18atoms/cm3
Life Time	≥ 10 micro seconds